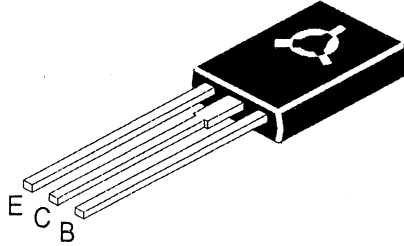


SILICON POWER DARLINGTON TRANSISTORS

(PNP) 2N6034, 2N6035, 2N6036
 (NPN) 2N6037, 2N6038, 2N6039

TO126
 Plastic Package



DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
2N6034, 2N6037	I_{CEX}	$V_{CE}=40V, V_{BE(off)}=1.5V$			100	μA
2N6035, 2N6038		$V_{CE}=60V, V_{BE(off)}=1.5V$			100	μA
2N6036, 2N6039		$V_{CE}=80V, V_{BE(off)}=1.5V$			100	μA
$T_C=125^\circ C$						
2N6034, 2N6037		$V_{CE}=40V, V_{BE(off)}=1.5V$			500	μA
2N6035, 2N6038		$V_{CE}=60V, V_{BE(off)}=1.5V$			500	μA
2N6036, 2N6039		$V_{CE}=80V, V_{BE(off)}=1.5V$			500	μA
Collector cut off Current						
2N6034, 2N6037	I_{CBO}	$V_{CB}=40, I_E=0$			0.5	mA
2N6035, 2N6038		$V_{CB}=60, I_E=0$			0.5	mA
2N6036, 2N6039		$V_{CB}=80, I_E=0$			0.5	mA
Emitter Cut off Current	I_{EBO}	$V_{BE}=5V, I_C=0$			2.0	mA
DC Current Gain	h_{FE}	$I_C=0.5A, V_{CE}=3V$	500			
		$I_C=2A, V_{CE}=3V$	750		15000	
		$I_C=4A, V_{CE}=3V$	100			
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2A, I_B=8mA$			2.0	V
		$I_C=4A, I_B=40mA$			3.0	V
Base Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=4A, I_B=40mA$			4.0	V
Base Emitter on Voltage	$V_{BE(on)}$	$I_C=2A, I_B=V_{CE}=3V$			2.8	V
Dynamic Characteristics						
Small Signal Current Gain	$ h_{fe} $	$I_C=0.75A, V_{CE}=10V$ $f=1MHz$	25			
Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0,$ $f=0.1MHz$			200	pF
	PNP				100	pF
	NPN					

